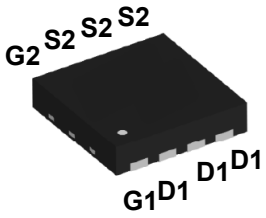
GOOD-ARK SEMICONDUCTOR

SSFN3010H

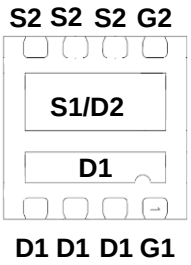
30V Dual N-Channel MOSFETs

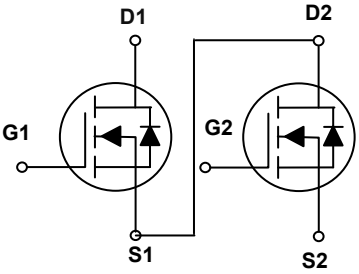
Main Product Characteristics

V_{DSS}	30V
$R_{DSON(max.)}$	10.5mΩ
I_D	19.5A



DFN3X3





Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The SSFN3010H utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous (T_C=25°C)	I_D	19.5	A
Drain Current-Continuous (T_C=100°C)		12.3	
Drain Current-Continuous (T_A=25°C)		10.8	
Drain Current-Continuous (T_A=100°C)		6.8	
Drain Current-Pulsed[1]	I_{DM}	78	A
Single Pulse Avalanche Energy[2]	E_{AS}	13	mJ
Single Pulse Avalanche Current[2]	I_{AS}	16	A
Power Dissipation (T_C=25°C)	P_D	27	W
Power Dissipation-Derate above 25°C		0.01	W/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.6	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On/Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C, I_D=1mA	-	0.04	-	V/°C
Drain-Source Leakage Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V, T_J=25°C	-	-	1	μA
		V_{DS}=24V, V_{GS}=0V, T_J=125°C	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	8.4	10.5	mΩ
		V_{GS}=4.5V, I_D=5A	-	10.8	14	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D =250uA	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	-4	-	mV/°C
Forward Transconductance	g_{fs}	V_{DS}=5V, I_D=5A	-	12	-	S
Dynamic and Switching Characteristics						
Total Gate Charge[3,4]	Q_g	V_{DS}=15V, I_D=5A V_{GS}=10V	-	15.6	31	nC
Gate-Source Charge[3,4]	Q_{gs}		-	2.3	5	
Gate-Drain Charge[3,4]	Q_{gd}		-	3	6	
Turn-On Delay Time[3,4]	$t_{d(on)}$	V_{DD}=15V, R_G=6Ω V_{GS}=10V, I_D=1A	-	3.8	7	nS
Rise Time[3,4]	t_r		-	10	19	
Turn-Off Delay Time[3,4]	$t_{d(off)}$		-	22	42	
Fall Time[3,4]	t_f		-	6.6	13	
Input Capacitance	C_{lss}	V_{DS}=25V, V_{GS}=0V, F=1MHz	-	620	900	pF
Output Capacitance	C_{oss}		-	85	125	
Reverse Transfer Capacitance	C_{rss}		-	60	90	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	-	2.8	5.6	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	-	-	19.5	A
Pulsed Source Current[3]	I_{SM}		-	-	39	A
Diode Forward Voltage[3]	V_{SD}	V_{GS}=0V, I_S=1A, T_J=25°C	-	-	1	V

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, Q1:I_{AS}=16A, Q2:I_{AS}=42A, R_G=25Ω, starting T_J=25°C.
3. Pulse test: pulse width≤300us, duty cycle≤2%.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

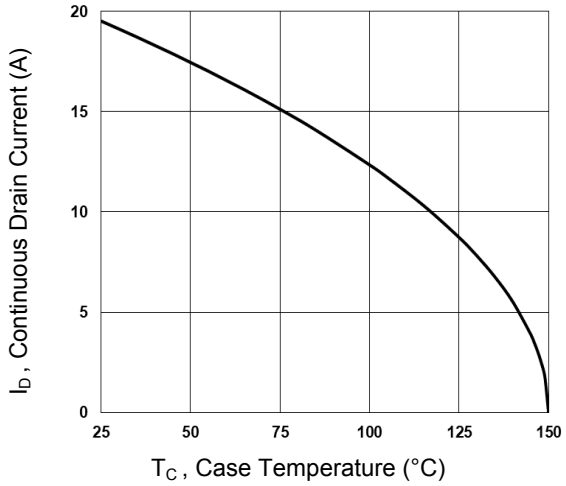


Figure 1. Continuous Drain Current vs. T_C

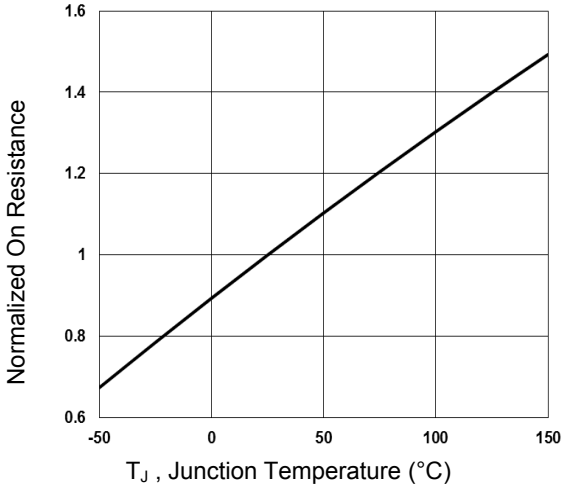


Figure 2. Normalized R_{DSON} vs. T_J

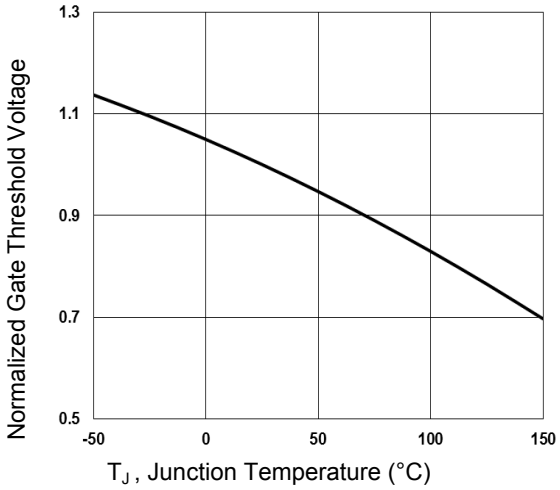


Figure 3. Normalized V_{th} vs. T_J

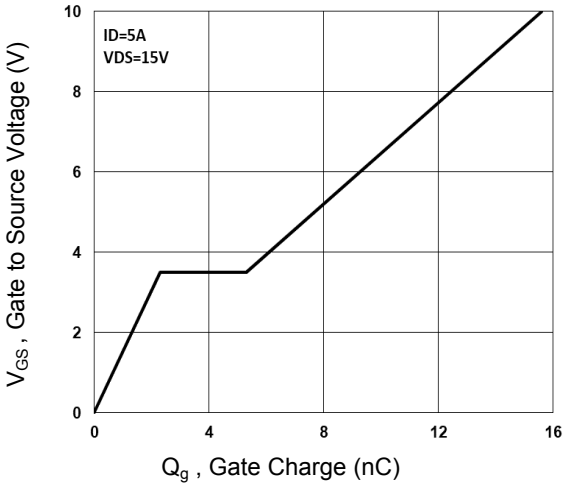


Figure 4. Gate Charge Waveform

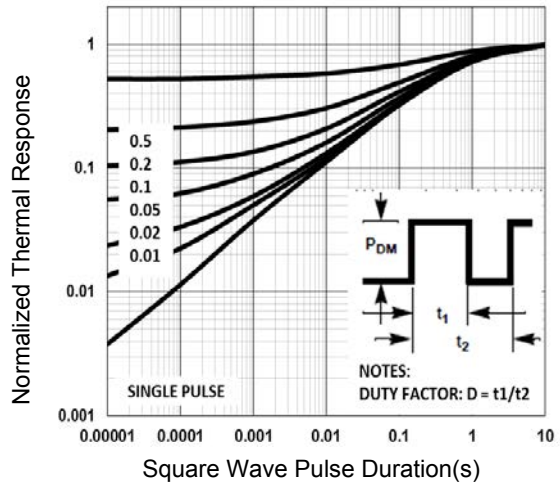


Figure 5. Normalized Transient Impedance

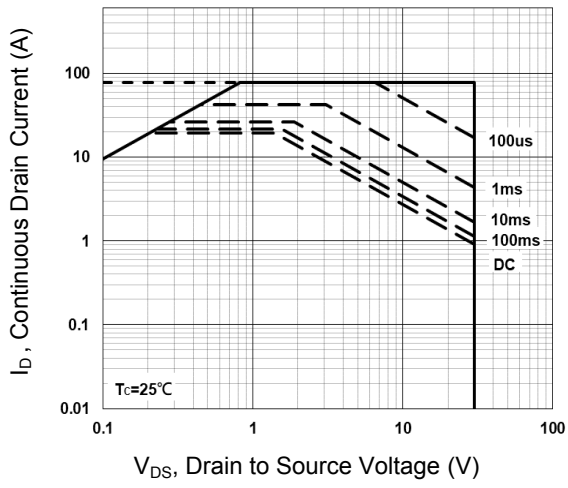


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

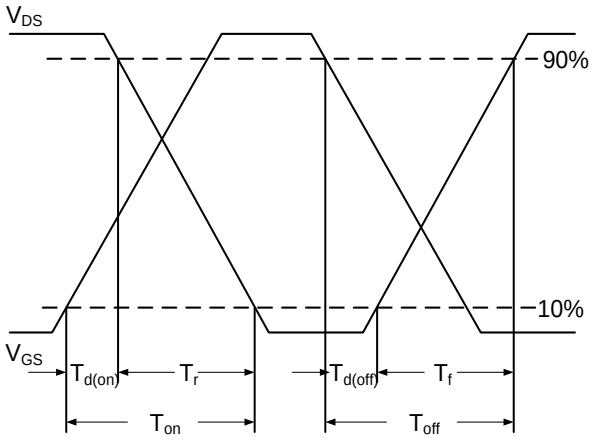


Figure 7. Switching Time Waveform

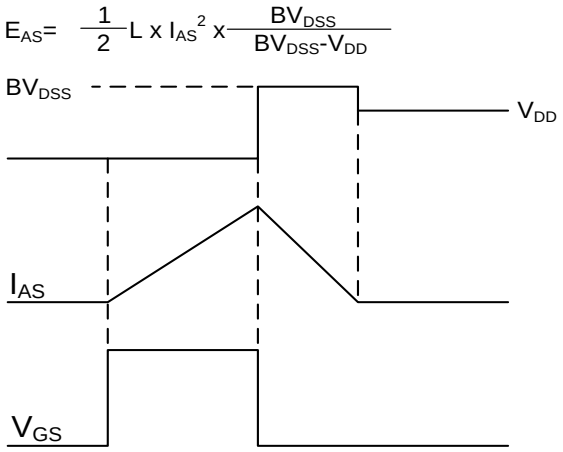
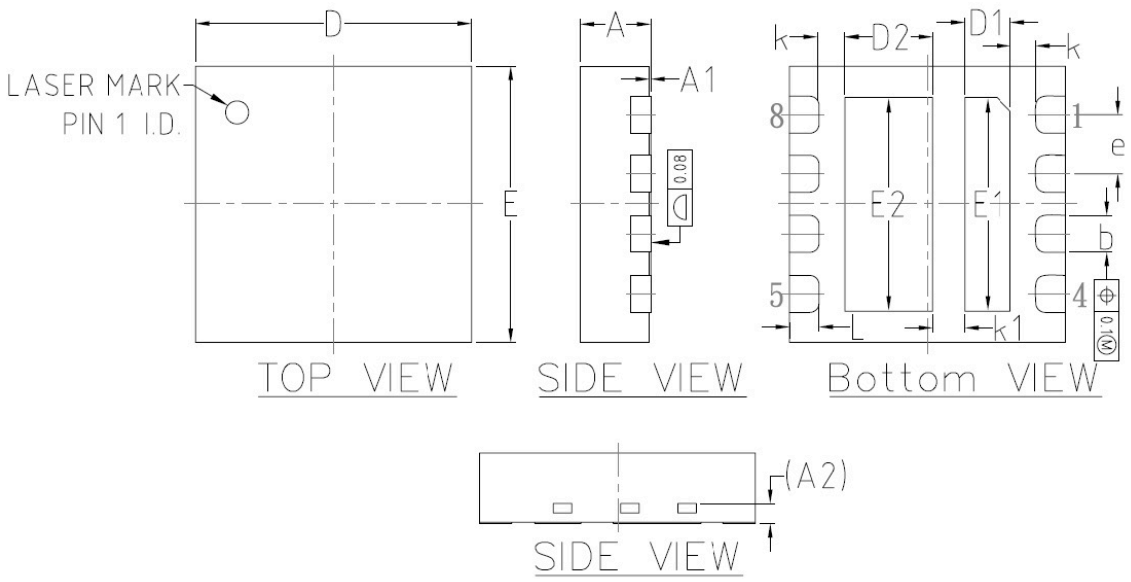


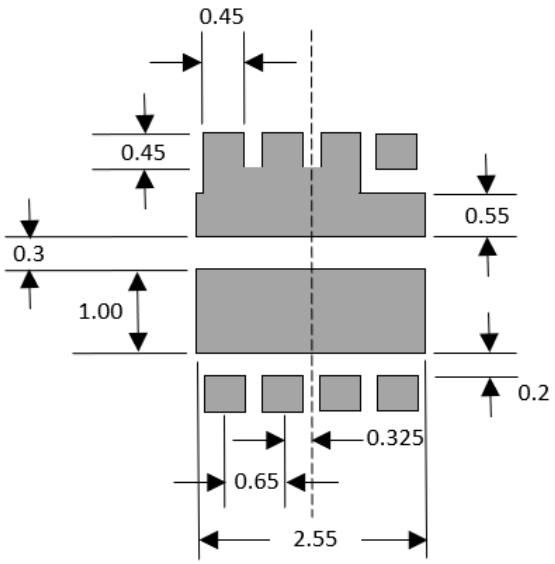
Figure 8. EAS Waveform

Package Outline Dimensions DFN3X3 Dual Pin



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	-	0.05
A2	0.20REF		
b	0.35	0.40	0.45
D	2.90	3.00	3.10
D1	0.40	0.50	0.60
D2	0.85	0.95	1.05
E	2.90	3.00	3.10
E1	2.20	2.30	2.40
E2	2.20	2.33	2.45
e	0.55	0.65	0.75
k	0.15	0.28	0.40
k1	0.25	0.35	0.45
L	0.27	-	0.40

Recommended Pad Layout



Unit:mm

Order Information

Device	Package	Marking	Carrier	Quantity	HSF Status
SSFN3010H	DFN3x3	DB3010H	Tape & Reel	3000 pcs / Reel	RoHS Compliant